



Rev.A May.-2020

DFN 3×3A-8L 塑封封装 P 沟道 MOS 场效应管。

P-Channel Enhancement Mode Field Effect Transistor in a DFN 3×3A-8L Plastic Package.

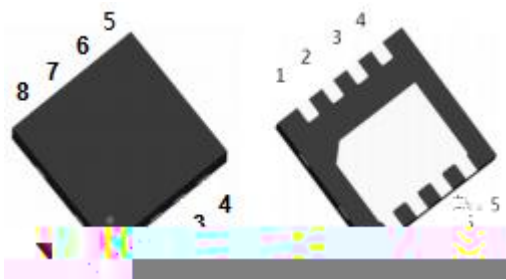
$V_{DS} (V) = -30V$

$I_D = -19 A (V_{GS} = -20V)$

无卤产品。HF Product.

用于电源管理，便携式设备和电池供电系统。

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

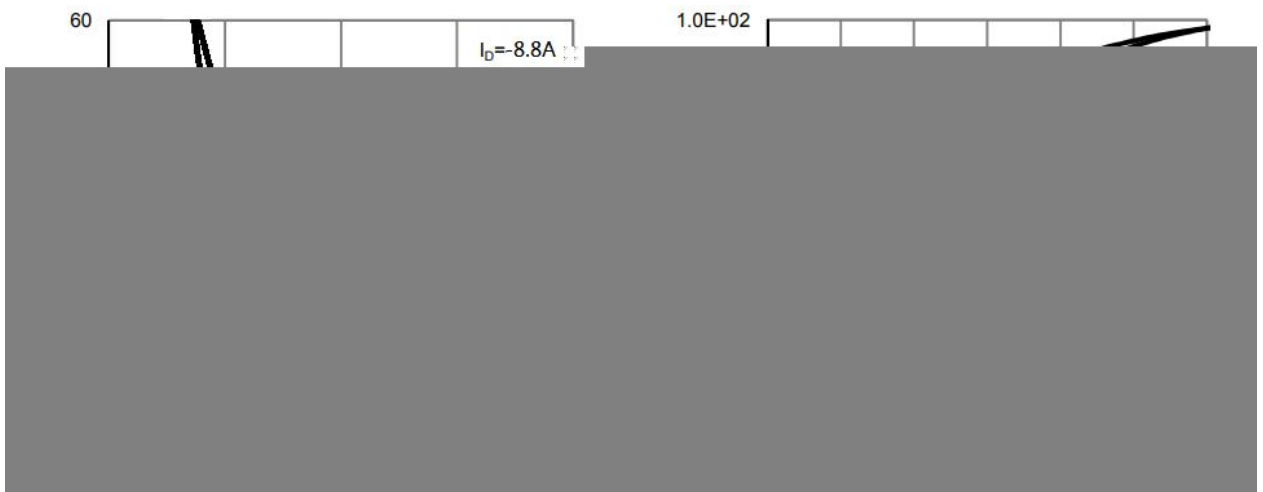


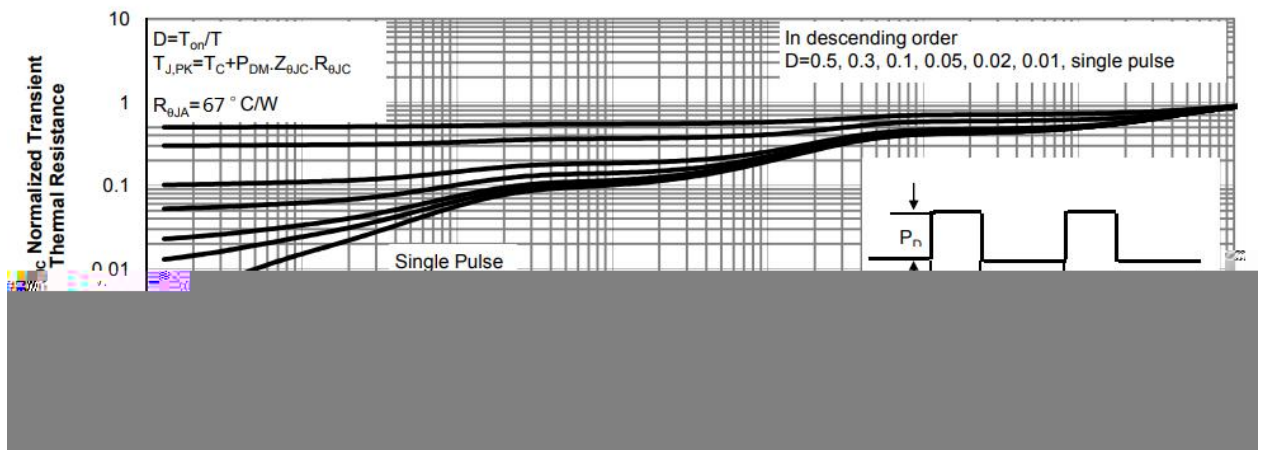
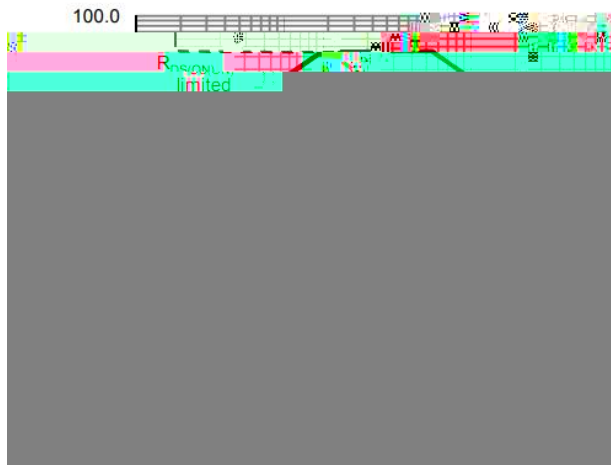
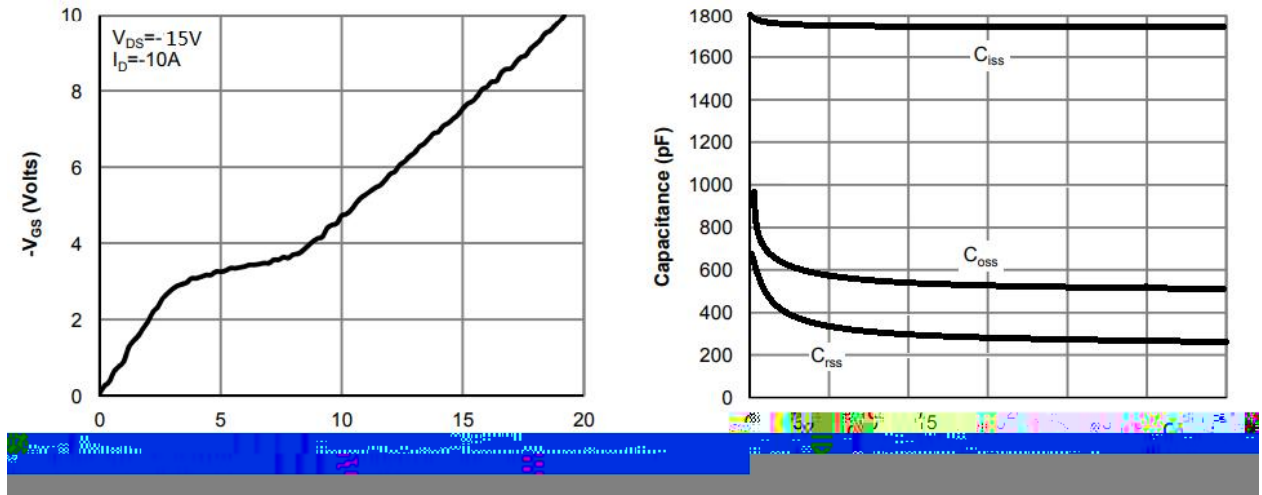
出脚	定义
Pin1	S
Pin2	S
Pin3	S
Pin4	G
Pin5	D
Pin6	D
Pin7	D
Pin8	D

见印章说明 See Marking Instructions.



参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current	$I_D (T_a=25^\circ\text{C})$	-19 h	A
Continuous Drain Current	$I_D (T_a=70^\circ\text{C})$	-14	A
Pulsed Drain Current ⁵ ^F	I_{DM}	-56	A
Avalanche energy L=0.5mH	E_{AS}	170	mJ
Power Dissipation for Single Operation	$P_D (T_a=25^\circ\text{C})$	13	W
Power Dissipation for Single Operation	$P_D (T_a=100^\circ\text{C})$	5.2	W

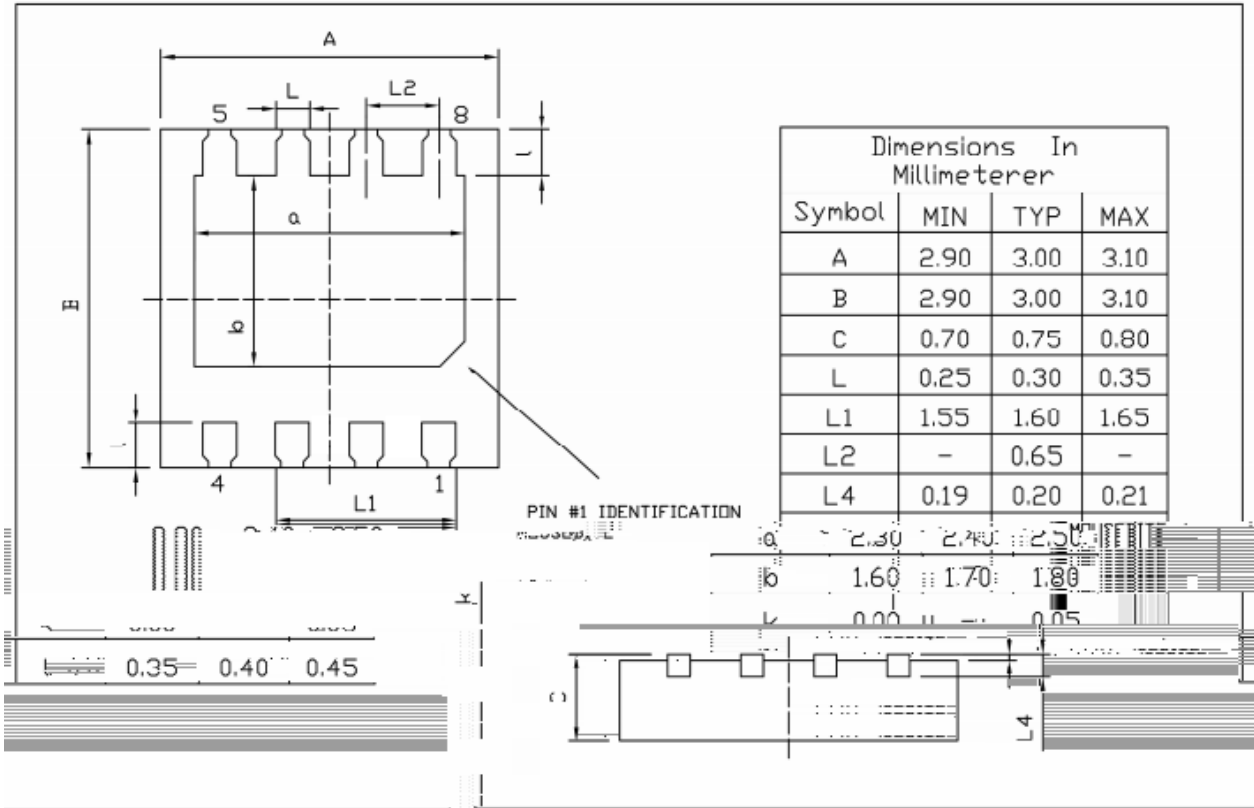






DFN3X3A-8L

Unit:mm





BR
200P03



BR

200P03

Note:

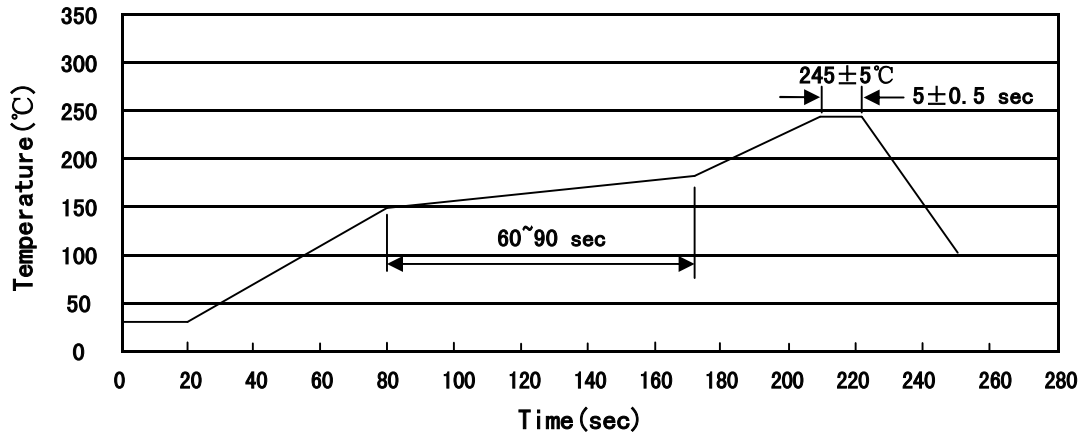
BR: Company Code.

200P03: Product Type

****: Lot No. Code, code change with Lot No



Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1 150 180 60 90sec; 1.Preheating:150~180°C, Time:60~90sec.
- 2 245±5 5±0.5sec; 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
- 3 2 10°C/sec. 3. Cooling Speed: 2~10°C/sec.

260±5°C 10±1 sec. Temp.:260±5°C Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
DFN 3 × 3A-8L	5,000	2	10,000	6	60,000	13" × 12	360×360×50	380×335×366